

TO-220-3L Plastic-Encapsulate MOSFETS

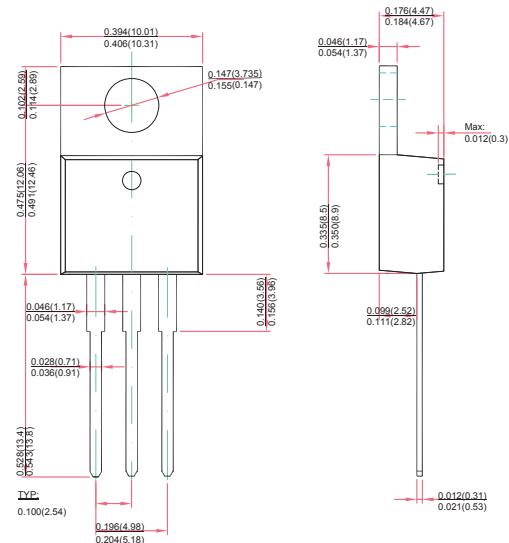
Features

- Low RDS(on)
- Lower Capacitances
- Lower Total Gate Charge
- Tighter VSD Specifications
- Avalanche Energy Specified
- 600V N-Channel MOSFET

MECHANICAL DATA

- Case style: TO-220-3L molded plastic
- Mounting position: any

TO-220-3L



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current	I _D	4.5	A
Single Pulsed Avalanche Energy (note1)	E _{AS}	250	mJ
Power Dissipation (note2,T _a =25°C)	P _D	2	W
Maximum Power Dissipation (note3,T _c =25°C)		120	
Thermal Resistance from Junction to Ambient	R _{θJA}	62.5	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-50 ~+150	

MOSFET ELECTRICAL CHARACTERISTICS $T_A=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Gate-Body Leakage Current (note 4)	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$			± 100	nA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	600			V
Gate-Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0		4.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$			1	μA
Forward transconductance	g_{fs}	$V_{DS}=40\text{V}, I_D=2.25\text{A}$	2.9			S
Drain-Source On-State Resistance	$R_{DS(\text{on})}$	$V_{GS}=10\text{V}, I_D=2.25\text{A}$			2.5	Ω
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$			670	pF
Output Capacitance	C_{oss}				72	
Reverse Transfer Capacitance	C_{rss}				8.5	
Turn-On Delay Time (note 4)	$t_{d(on)}$	$V_{DD}=300\text{V}, I_D=4.5\text{A}, R_G=25\Omega$			30	ns
Rise Time (note 4)	t_r				90	
Turn-Off Delay Time (note 4)	$t_{d(off)}$				85	
Fall Time (note 4)	t_f				100	
Forward on Voltage (note 4)	V_{SD}	$V_{GS}=0\text{V}, I_S=4.5\text{A}$			1.4	V

Notes:

- E_{AS} condition: $T_j=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, $L=16\text{mH}$, $I_{AS}=5\text{A}$
- This test is performed with no heat sink at $T_a=25^\circ\text{C}$.
- This test is performed with infinite heat sink at $T_c=25^\circ\text{C}$.
- Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.